

# Kenji Yoshino

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2604387/publications.pdf>

Version: 2024-02-01

198  
papers

5,926  
citations

126907

33  
h-index

79698

73  
g-index

199  
all docs

199  
docs citations

199  
times ranked

7042  
citing authors

#	ARTICLE	IF	CITATIONS
1	Relationship between Carrier Density and Precursor Solution Stirring for Lead-Free Tin Halide Perovskite Solar Cells Performance. <i>ACS Applied Energy Materials</i> , 2022, 5, 4002-4007.	5.1	10
2	Influence of charge transport layer on the crystallinity and charge extraction of pure tin-based halide perovskite film. <i>Journal of Energy Chemistry</i> , 2022, 69, 612-615.	12.9	2
3	Phase diagram of the Ag <sub>2</sub> SnS <sub>3</sub> -ZnS pseudobinary system for Ag <sub>2</sub> ZnSnS <sub>4</sub> crystal growth. <i>Journal of Crystal Growth</i> , 2021, 555, 125967.	1.5	6
4	Impact of Auger recombination on performance limitation of perovskite solar cell. <i>Solar Energy</i> , 2021, 217, 342-353.	6.1	27
5	Environmentally friendly thermoelectric sulphide Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals achieving a 1.6 dimensionless figure of merit $zT$ . <i>Journal of Materials Chemistry A</i> , 2021, 9, 15595-15604.	10.3	17
6	Solution growth of chalcopyrite Cu(In <sub>1-x</sub> Ga <sub>x</sub> )Se <sub>2</sub> single crystals for high open-circuit voltage photovoltaic device. <i>High Temperature Materials and Processes</i> , 2021, 40, 439-445.	1.4	0
7	Theoretical analysis of band alignment at back junction in Sn-Ge perovskite solar cells with inverted p-i-n structure. <i>Solar Energy Materials and Solar Cells</i> , 2020, 206, 110268.	6.2	66
8	Reducing trap density and carrier concentration by a Ge additive for an efficient quasi 2D/3D perovskite solar cell. <i>Journal of Materials Chemistry A</i> , 2020, 8, 2962-2968.	10.3	53
9	Growth and Characterization of Arsenic-Doped CdTe <sub>1-x</sub> Se <sub>x</sub> Single Crystals Grown by the Cd-Solvent Traveling Heater Method. <i>Journal of Electronic Materials</i> , 2020, 49, 6971-6976.	2.2	2
10	Surface-Modified Graphene Oxide/Lead Sulfide Hybrid Film-Forming Ink for High-Efficiency Bulk Nano-Heterojunction Colloidal Quantum Dot Solar Cells. <i>Nano-Micro Letters</i> , 2020, 12, 111.	27.0	16
11	Hot-injection and ultrasonic irradiation syntheses of Cs <sub>2</sub> SnI <sub>6</sub> quantum dot using Sn long-chain amino-complex. <i>Journal of Nanoparticle Research</i> , 2020, 22, 1.	1.9	5
12	Enhanced Device Performance with Passivation of the TiO <sub>2</sub> Surface Using a Carboxylic Acid Fullerene Monolayer for a SnPb Perovskite Solar Cell with a Normal Planar Structure. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 17776-17782.	8.0	24
13	Stability Improvement of Perovskite Solar Cells by Adding Sb-Xanthate to Precursor Solution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2000144.	1.8	3
14	Lead-free tin-halide perovskite solar cells with 13% efficiency. <i>Nano Energy</i> , 2020, 74, 104858.	16.0	347
15	Comparison of Sb, As, and P doping in Cd-rich CdTe single crystals: Doping properties, persistent photoconductivity, and long-term stability. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	18
16	Preparation of a CuGaSe <sub>2</sub> single crystal and its photocathodic properties. <i>RSC Advances</i> , 2020, 10, 40310-40315.	3.6	7
17	Chalcostibite Single-Crystal CuSbS <sub>2</sub> as High-Performance Thermoelectric Material. <i>Materials Transactions</i> , 2020, 61, 2407-2411.	1.2	6
18	Relationship between Lattice Strain and Efficiency for Sn-Perovskite Solar Cells. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 31105-31110.	8.0	101

#	ARTICLE	IF	CITATIONS
19	Suppression of Charge Carrier Recombination in Lead-Free Tin Halide Perovskite via Lewis Base Post-treatment. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 5277-5283.	4.6	196
20	The Effect of Transparent Conductive Oxide Substrate on the Efficiency of SnGe-perovskite Solar Cells. <i>Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]</i> , 2019, 32, 597-602.	0.3	5
21	Pb-free Sn Perovskite Solar Cells Doped with Samarium Iodide. <i>Chemistry Letters</i> , 2019, 48, 836-839.	1.3	6
22	Arsenic doped Cd-rich CdTe: equilibrium doping limit and long lifetime for high open-circuit voltage solar cells greater than 900 mV. <i>Applied Physics Express</i> , 2019, 12, 081002.	2.4	6
23	Improving Photovoltaic Performance of ZnO Nanowires Based Colloidal Quantum Dot Solar Cells via SnO <sub>2</sub> Passivation Strategy. <i>Frontiers in Energy Research</i> , 2019, 7, .	2.3	19
24	Growth of CuSbS <sub>2</sub> Single Crystal as an Environmentally Friendly Thermoelectric Material. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800861.	1.8	10
25	Micro-scale current path distributions of Zn <sup>1</sup> -Mg O-coated SnO <sub>2</sub> :F transparent electrodes prepared by sol-gel and sputtering methods in perovskite solar cells. <i>Thin Solid Films</i> , 2019, 669, 455-460.	1.8	5
26	Role of GeI <sub>2</sub> and SnF <sub>2</sub> additives for SnGe perovskite solar cells. <i>Nano Energy</i> , 2019, 58, 130-137.	16.0	104
27	Ge <sub>2</sub> Additive for High Optoelectronic Quality CsPbI <sub>3</sub> Quantum Dots and Their Application in Photovoltaic Devices. <i>Chemistry of Materials</i> , 2019, 31, 798-807.	6.7	112
28	Surface Coatings for Improving Solar Cell Efficiencies. , 2019, , .		0
29	Ultrafast Electron Injection from Photoexcited Perovskite CsPbI <sub>3</sub> QDs into TiO <sub>2</sub> Nanoparticles with Injection Efficiency near 99%. <i>Journal of Physical Chemistry Letters</i> , 2018, 9, 294-297.	4.6	75
30	Highly Efficient 17.6% Tin-Lead Mixed Perovskite Solar Cells Realized through Spike Structure. <i>Nano Letters</i> , 2018, 18, 3600-3607.	9.1	114
31	Understanding charge transfer and recombination by interface engineering for improving the efficiency of PbS quantum dot solar cells. <i>Nanoscale Horizons</i> , 2018, 3, 417-429.	8.0	50
32	Mixed Sn-Ge Perovskite for Enhanced Perovskite Solar Cell Performance in Air. <i>Journal of Physical Chemistry Letters</i> , 2018, 9, 1682-1688.	4.6	206
33	Growth Mechanism of ZnO Thin Films Grown by Spray Pyrolysis Using Diethylzinc Solution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700406.	1.8	2
34	Enhancement of charge transport in quantum dots solar cells by N-butylamine-assisted sulfur-crosslinking of PbS quantum dots. <i>Solar Energy</i> , 2018, 174, 399-408.	6.1	11
35	Enhanced performance of ZnO based perovskite solar cells by Nb <sub>2</sub> O <sub>5</sub> surface passivation. <i>Organic Electronics</i> , 2018, 62, 615-620.	2.6	20
36	Effect of the conduction band offset on interfacial recombination behavior of the planar perovskite solar cells. <i>Nano Energy</i> , 2018, 53, 17-26.	16.0	110

#	ARTICLE	IF	CITATIONS
37	Solution-Processed Air-Stable Copper Bismuth Iodide for Photovoltaics. ChemSusChem, 2018, 11, 2930-2935.	6.8	39
38	Investigation of Interfacial Charge Transfer in Solution Processed Cs <sub>2</sub> SnI <sub>6</sub> Thin Films. Journal of Physical Chemistry C, 2017, 121, 13092-13100.	3.1	66
39	Atmospheric growth of ZnO films deposited by spray pyrolysis using diethylzinc solution. Journal of Crystal Growth, 2017, 468, 473-476.	1.5	10
40	Colloidal Synthesis of Air-Stable Alloyed CsSn <sub>1-x</sub> Pb <sub>x</sub> I <sub>3</sub> Perovskite Nanocrystals for Use in Solar Cells. Journal of the American Chemical Society, 2017, 139, 16708-16719.	13.7	314
41	Slow hot carrier cooling in cesium lead iodide perovskites. Applied Physics Letters, 2017, 111, .	3.3	56
42	Highly Luminescent Phase-Stable CsPbI <sub>3</sub> Perovskite Quantum Dots Achieving Near 100% Absolute Photoluminescence Quantum Yield. ACS Nano, 2017, 11, 10373-10383.	14.6	748
43	Group-V doping impact on Cd-rich CdTe single crystals grown by traveling-heater method. , 2017, , .		0
44	Annealing effects on Ga-doped ZnO thin films grown by atmospheric spray pyrolysis using diethylzinc solution. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1600177.	0.8	0
45	Cation ratio fluctuations in Cu <sub>2</sub> ZnSnS <sub>4</sub> at the 20-nm length scale investigated by analytical electron microscopy. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2392-2399.	1.8	11
46	Damage repair of lens surface in CPV by silica based coating. AIP Conference Proceedings, 2016, , .	0.4	1
47	Near IR sensitive Sn based perovskite solar cells with high current density reaching 30mA/cm <sup>2</sup> . , 2016, , .		1
48	Growth and characterization of indium-doped Zn <sub>3</sub> P <sub>2</sub> bulk crystals. Japanese Journal of Applied Physics, 2016, 55, 041201.	1.5	12
49	Na-doped Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal grown by traveling-heater method. Journal of Crystal Growth, 2016, 453, 119-123.	1.5	14
50	Architecture of the Interface between the Perovskite and Hole-Transport Layers in Perovskite Solar Cells. ChemSusChem, 2016, 9, 2634-2639.	6.8	27
51	Facile Synthesis and Characterization of Sulfur Doped Low Bandgap Bismuth Based Perovskites by Soluble Precursor Route. Chemistry of Materials, 2016, 28, 6436-6440.	6.7	87
52	Low-temperature Growth of Porous and Dense ZnO Films for Perovskite Solar Cells on ITO Substrate. Chemistry Letters, 2016, 45, 176-178.	1.3	3
53	Free-carrier dynamics and band tails in Cu <sub>2</sub> ZnSn(S <sub>x</sub> Se <sub>1-x</sub> ) <sub>4</sub> : Evaluation of factors determining solar cell efficiency. Physical Review B, 2015, 92, .	3.2	19
54	Photocarrier dynamics in undoped and Na-doped Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals revealed by ultrafast time-resolved terahertz spectroscopy. Applied Physics Express, 2015, 8, 062303.	2.4	14

#	ARTICLE	IF	CITATIONS
55	Photoelectrical properties of undoped and Na-doped Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals measured by optical time-resolved spectroscopy. , 2015, , .		1
56	Growth and characterization of Cu <sub>2</sub> ZnSn(S Se1 <sup>~</sup> ) <sub>4</sub> single crystal grown by traveling heater method. Journal of Crystal Growth, 2015, 423, 9-15.	1.5	11
57	Solution growth of chalcopyrite compounds single crystal. Renewable Energy, 2015, 79, 127-130.	8.9	9
58	Optical absorption, charge separation and recombination dynamics in Sn/Pb cocktail perovskite solar cells and their relationships to photovoltaic performances. Journal of Materials Chemistry A, 2015, 3, 9308-9316.	10.3	85
59	Characterization of CuInS <sub>2</sub> thin films prepared from materials grown by using the mechanochemical method and their photovoltaic applications. Japanese Journal of Applied Physics, 2015, 54, 08KC19.	1.5	0
60	Preparation of Cu <sub>2</sub> ZnSn <sub>4</sub> Thin Films using Copper Naphthenate, Zinc Naphthenate, and Tin Octoate as Starting Materials. IEEJ Transactions on Fundamentals and Materials, 2015, 135, 318-319.	0.2	0
61	Effect of hydrogen partial pressure on growth of Cu <sub>2</sub> ZnSn <sub>4</sub> films sulfurized using diethyl sulfide. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1198-1201.	0.8	3
62	Polarized Raman spectroscopy of Cu-poor and Zn-rich single-crystal Cu <sub>2</sub> ZnSnSe <sub>4</sub> . Applied Physics Letters, 2014, 105, .	3.3	23
63	Control of Charge Dynamics through a Charge Separation Interface for All-Solid Perovskite-Sensitized Solar Cells. ChemPhysChem, 2014, 15, 1062-1069.	2.1	73
64	Temperature-dependent photocarrier recombination dynamics in Cu <sub>2</sub> ZnSn <sub>4</sub> single crystals. Applied Physics Letters, 2014, 104, 081907.	3.3	23
65	All-Solid Perovskite Solar Cells with HOCO-R-NH <sub>3</sub> <sup>+</sup> Anchor-Group Inserted between Porous Titania and Perovskite. Journal of Physical Chemistry C, 2014, 118, 16651-16659.	3.1	191
66	Thermo-physical properties of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Journal of Crystal Growth, 2014, 393, 167-170.	1.5	21
67	Growth and characterization of Cu <sub>2</sub> ZnSn(S Se1 <sup>~</sup> ) <sub>4</sub> alloys grown by the melting method. Journal of Crystal Growth, 2014, 386, 204-207.	1.5	20
68	Growth and Characterization of ZnS Films by Chemical Bath Deposition. Advanced Materials Research, 2014, 894, 416-420.	0.3	1
69	Fabrication of an efficient electrodeposited Cu <sub>2</sub> ZnSnS <sub>4</sub> -based solar cells with more than 6% conversion efficiency using a sprayed Ga-doped ZnO window layer. RSC Advances, 2014, 4, 24351-24355.	3.6	9
70	Effects of sodium on electrical properties in Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Applied Physics Letters, 2014, 104, .	3.3	113
71	All-solid Sn/Pb halide perovskite sensitized solar cells. , 2014, , .		0
72	Charge transfer and recombination at the metal oxide/CH <sub>3</sub> NH <sub>3</sub> PbCl <sub>2</sub> /spiro-OMeTAD interfaces: uncovering the detailed mechanism behind high efficiency solar cells. Physical Chemistry Chemical Physics, 2014, 16, 19984-19992.	2.8	88

#	ARTICLE	IF	CITATIONS
73	Radiation tolerance of Si <sub>1-x</sub> Ge <sub>x</sub> source/drain n-type metal oxide semiconductor field effect transistors with different carbon concentrations. <i>Thin Solid Films</i> , 2014, 557, 307-310.	1.8	2
74	CH <sub>3</sub> NH <sub>3</sub> Sn <sub>2</sub> Pb <sub>3</sub> (1-x)I <sub>3</sub> Perovskite Solar Cells Covering up to 1060 nm. <i>Journal of Physical Chemistry Letters</i> , 2014, 5, 1004-1011.	4.6	852
75	Growth and characterization of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013, 210, 1328-1331.	1.8	26
76	Photocarrier localization and recombination dynamics in Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	34
77	Correlation between intrinsic defects and electrical properties in the high-quality Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	69
78	Optical and electrical characterization of transparent Ga-doped ZnO thin films grown by atmospheric spray pyrolysis using diethylzinc solution. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1015-1018.	0.8	3
79	Huge suppression of charge recombination in P3HT-ZnO organic-inorganic hybrid solar cells by locating dyes at the ZnO/P3HT interfaces. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 14370.	2.8	33
80	Single-step fabrication of all-solid dye-sensitized solar cells using solution-processable precursor. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013, 210, 1846-1850.	1.8	3
81	Controlling the processable ZnO and polythiophene interface for dye-sensitized thin film organic solar cells. <i>Thin Solid Films</i> , 2013, 536, 302-307.	1.8	10
82	Excitonic emissions of AgInS <sub>2</sub> crystals with chalcopyrite and orthorhombic structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1042-1045.	0.8	2
83	Increased Radiation Hardness of Short-Channel Electron-Irradiated Si <sub>1-x</sub> Ge <sub>x</sub> Source/Drain p-Type Metal Oxide Semiconductor Field-Effect Transistors at Higher Ge Content. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 094201.	1.5	0
84	Growth and characterization of ZnS films by spray pyrolysis. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1102-1106.	0.8	10
85	Electrical properties of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. , 2013, , .		0
86	Preparation of CuInS <sub>2</sub> thin films from materials grown by mechanochemical method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1019-1022.	0.8	1
87	Ge content dependence of radiation damage in Si <sub>1-x</sub> Ge <sub>x</sub> source/drain p-type metal oxide semiconductor field effect transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1148-1151.	0.8	5
88	Characterization of Spin Coated Nondoped and In-Doped ZnO Films Using Novel Precursor Solution. <i>Materials Science Forum</i> , 2012, 725, 277-280.	0.3	2
89	Temperature Dependence of Linear Thermal Expansion of CuGaSe <sub>2</sub> Crystals. <i>Materials Science Forum</i> , 2012, 725, 171-174.	0.3	2
90	Effect of H <sub>2</sub> S Annealing on Sb-Doped CuInS <sub>2</sub> Thin Films Prepared by Vacuum Evaporation. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 10NC19.	1.5	0

#	ARTICLE	IF	CITATIONS
91	Thickness Dependence of Structure and Optical Characteristics in Fluorine-Doped SnO <sub>2</sub> Films Grown by Spray Pyrolysis Method. Japanese Journal of Applied Physics, 2012, 51, 125503.	1.5	3
92	Mn-doping effect of photoluminescence on AgInS <sub>2</sub> . Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2355-2357.	0.8	0
93	Characterization of AgInS <sub>2</sub> thin films prepared by vacuum evaporation. Physica B: Condensed Matter, 2012, 407, 2858-2860.	2.7	6
94	Preparation of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals from Sn solutions. Journal of Crystal Growth, 2012, 341, 38-41.	1.5	69
95	Growth of Cu <sub>2</sub> ZnSnSe <sub>4</sub> single crystals from Sn solutions. Journal of Crystal Growth, 2012, 354, 147-151.	1.5	41
96	Local compressive stress generation in electron irradiated boron-doped Si <sub>0.75</sub> Ge <sub>0.25</sub> /Si devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2058-2061.	0.8	1
97	Radiation damage of Si <sub>1-x</sub> Ge <sub>x</sub> S/D p-type metal oxide semiconductor field effect transistor with different Ge concentrations. Thin Solid Films, 2012, 520, 3337-3340.	1.8	9
98	Effect of H <sub>2</sub> S Annealing on Sb-Doped CuInS Thin Films Prepared by Vacuum Evaporation. Japanese Journal of Applied Physics, 2012, 51, 10NC19.	1.5	1
99	Thickness Dependence of Structure and Optical Characteristics in Fluorine-Doped SnO <sub>2</sub> Films Grown by Spray Pyrolysis Method. Japanese Journal of Applied Physics, 2012, 51, 125503.	1.5	3
100	Effect of Dimethylselenium Supply Rate on Growth of Cu(In, Ga)Se <sub>2</sub> Films. IEICE Transactions on Electronics, 2012, E95.C, 1304-1306.	0.6	0
101	Growth of Cu(In,Ga)Se <sub>2</sub> Films Selenized Using Dimethylselenium. Materials Transactions, 2012, 53, 1169-1171.	1.2	0
102	Characteristic of Low Resistivity Fluorine-Doped SnO <sub>2</sub> Thin Films Grown by Spray Pyrolysis. Japanese Journal of Applied Physics, 2011, 50, 05FB15.	1.5	5
103	Growth of Cu <sub>2</sub> ZnSnS <sub>4</sub> Single Crystal by Traveling Heater Method. Japanese Journal of Applied Physics, 2011, 50, 128001.	1.5	17
104	Growth of IrO <sub>x</sub> /SnO <sub>x</sub> Films Deposited by Reactive Sputtering. Japanese Journal of Applied Physics, 2011, 50, 05FB14.	1.5	2
105	Low-Temperature Growth of ZnO Films by Spray Pyrolysis. Japanese Journal of Applied Physics, 2011, 50, 040207.	1.5	12
106	Water-Repellent Silicon Surface with Nanostructure Formed by Catalysis of Single Nanosized Silver Particle. Japanese Journal of Applied Physics, 2011, 50, 128003.	1.5	0
107	Low Sheet Resistivity of Transparent Ga-Doped ZnO Film Grown by Atmospheric Spray Pyrolysis. Japanese Journal of Applied Physics, 2011, 50, 088001.	1.5	4
108	Growth of Spin-Coated ZnO Films Using Diethylzinc Solution. Japanese Journal of Applied Physics, 2011, 50, 108001.	1.5	1

#	ARTICLE	IF	CITATIONS
109	Peculiarities of Linear Thermal Expansion of CuInS <sub>2</sub> Single Crystals. Japanese Journal of Applied Physics, 2011, 50, 05FB04.	1.5	8
110	Photoluminescence Study of AgInS <sub>2</sub> by Using Confocal Microscopy System. Japanese Journal of Applied Physics, 2011, 50, 05FC04.	1.5	0
111	Effect of H <sub>2</sub> S Annealing on Ag-Rich Ag-In-S Thin Films Prepared by Vacuum Evaporation. Japanese Journal of Applied Physics, 2011, 50, 05FB06.	1.5	1
112	Low-Temperature Growth of ZnO Films by Spray Pyrolysis. Japanese Journal of Applied Physics, 2011, 50, 040207.	1.5	8
113	Peculiarities of Linear Thermal Expansion of CuInS <sub>2</sub> Single Crystals. Japanese Journal of Applied Physics, 2011, 50, 05FB04.	1.5	14
114	Characteristic of Low Resistivity Fluorine-Doped SnO <sub>2</sub> Thin Films Grown by Spray Pyrolysis. Japanese Journal of Applied Physics, 2011, 50, 05FB15.	1.5	4
115	Low Sheet Resistivity of Transparent Ga-Doped ZnO Film Grown by Atmospheric Spray Pyrolysis. Japanese Journal of Applied Physics, 2011, 50, 088001.	1.5	4
116	Growth of Spin-Coated ZnO Films Using Diethylzinc Solution. Japanese Journal of Applied Physics, 2011, 50, 108001.	1.5	3
117	Effect of H <sub>2</sub> S Annealing on Ag-Rich Ag-In-S Thin Films Prepared by Vacuum Evaporation. Japanese Journal of Applied Physics, 2011, 50, 05FB06.	1.5	0
118	Growth of Cu <sub>2</sub> ZnSnS <sub>4</sub> Single Crystal by Traveling Heater Method. Japanese Journal of Applied Physics, 2011, 50, 128001.	1.5	3
119	Electron Scattering Mechanism of FTO Films Grown by Spray Pyrolysis Method. Journal of Electronic Materials, 2010, 39, 819-822.	2.2	38
120	Degradation of GaN LEDs by electron irradiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 57-60.	3.5	15
121	Effect of annealing for Ag-In-S thin films prepared by a vacuum evaporation method. , 2010, , .		1
122	Growth of AgInS <sub>2</sub> crystals grown by hot-press method. , 2009, , .		0
123	Dependence of thickness F-doped SnO <sub>2</sub> films grown by spray pyrolysis technique. , 2009, , .		0
124	Double band structure of ZnSe/CdSe/ZnSe quantum dots for photovoltaic devices. , 2009, , .		0
125	Optical characterization of Ag/Ga composition ratio in AgGaSe <sub>2</sub> thin film. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1070-1073.	0.8	1
126	Characterization of proton irradiated AgInSe <sub>2</sub> thin film. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1067-1069.	0.8	4



#	ARTICLE	IF	CITATIONS
127	Optical and electrical characterization of In-doped ZnMgO films grown by spray pyrolysis method. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1120-1123.	0.8	2
128	Optical and electrical characterization of FTO films grown by spray pyrolysis method. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1124-1126.	0.8	13
129	Molecular beam epitaxial growth of ZnCrO films by using RF plasma source. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1012-1015.	0.8	2
130	Growth and characterization of Mn-doped AgInS <sub>2</sub> grown by a hot-press method. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1043-1046.	0.8	0
131	Effect of annealing for CuInS <sub>2</sub> thin films prepared from Cu-rich ternary compound. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1030-1033.	0.8	15
132	Analysis of bound-exciton emissions of CuInS <sub>2</sub> crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1093-1096.	0.8	1
133	Study of steady-state photoluminescence of AgInSe <sub>2</sub> crystals. Thin Solid Films, 2008, 517, 1445-1448.	1.8	9
134	Dependence of Cu/In ratio of structural and electrical characterization of CuInS <sub>2</sub> crystal. Journal of Materials Science: Materials in Electronics, 2008, 19, 301-304.	2.2	22
135	Growth and characterization of ZnSe/CdSe/ZnSe quantum dots fabricated by using an alternate molecular beam supplying method. Applied Surface Science, 2008, 254, 7913-7917.	6.1	0
136	Structural and magnetic characterization of Mn-doped ZnO films grown by spray pyrolysis method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 234-236.	3.5	12
137	Carrier induced magnetic anomalies in Mn-doped AgGaSe <sub>2</sub> magnetic semiconductor. Journal of Applied Physics, 2008, 103, 07D103.	2.5	1
138	Growth and Annealing of ZnO Films Grown by Spray Pyrolysis. Japanese Journal of Applied Physics, 2008, 47, 8170.	1.5	9
139	Emissions from Deep Levels in Hydrothermal Grown ZnO Substrates. Journal of the Korean Physical Society, 2008, 53, 2959-2962.	0.7	2
140	Dislocation of high-quality large DCP-ZnTe substrate examined by photoluminescence and X-ray topography. Materials Science in Semiconductor Processing, 2006, 9, 45-48.	4.0	0
141	Characterization of AgGaSe <sub>2</sub> thin films grown by post annealing method. Thin Solid Films, 2006, 515, 505-508.	1.8	19
142	Structural, electrical and optical properties of AgInS <sub>2</sub> thin films grown by thermal evaporation method. Journal of Physics and Chemistry of Solids, 2005, 66, 1858-1861.	4.0	44
143	Dependence of oxygen flow rate on piezoelectric photothermal spectra of ZnO thin films grown by a reactive plasma deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 70-73.	3.5	10
144	Structural and electrical characterization of AgInS <sub>2</sub> thin films grown by single-source thermal evaporation method. Journal of Materials Science: Materials in Electronics, 2005, 16, 393-396.	2.2	10

#	ARTICLE	IF	CITATIONS
145	Structural, optical and electrical characterization on ZnO film grown by a spray pyrolysis method. Journal of Materials Science: Materials in Electronics, 2005, 16, 403-408.	2.2	20
146	Dislocation of high quality P-doped ZnTe substrate examined by X-ray topography. Journal of Materials Science: Materials in Electronics, 2005, 16, 445-448.	2.2	2
147	Effects of substrate treatment and growth conditions on structure, morphology, and luminescence of homoepitaxial ZnTe deposited by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2004, 96, 1230-1237.	2.5	13
148	Proton-beam-induced defect levels in CuInSe <sub>2</sub> thin-film absorbers: An investigation on nonradiative electron transitions. Applied Physics Letters, 2004, 85, 1347-1349.	3.3	3
149	Annealing effects of a high-quality ZnTe substrate. Journal of Electronic Materials, 2004, 33, 579-582.	2.2	21
150	Proton irradiation damages in CuInSe <sub>2</sub> thin film solar cell materials by a piezoelectric photothermal spectroscopy. Solid-State Electronics, 2004, 48, 1815-1818.	1.4	9
151	Structural and optical characterization of CuInS <sub>2</sub> thin films grown by vacuum evaporation method. Journal of Materials Science: Materials in Electronics, 2003, 14, 291-294.	2.2	6
152	Title is missing!. Journal of Materials Science: Materials in Electronics, 2003, 14, 421-425.	2.2	1
153	Optical and electrical characterization of high-quality P-doped ZnTe substrates. Physica B: Condensed Matter, 2003, 340-342, 254-257.	2.7	8
154	Growth and characterization of p-type AgInS <sub>2</sub> crystals. Journal of Physics and Chemistry of Solids, 2003, 64, 1839-1842.	4.0	58
155	Impurity levels of high quality p-doped ZnTe single crystal. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 631-634.	0.8	2
156	Structural and optical characterization of Sb-doped CuInS <sub>2</sub> thin films grown by vacuum evaporation method. Journal of Physics and Chemistry of Solids, 2003, 64, 1863-1867.	4.0	38
157	MOVPE growth and characterisation of ZnTe epilayers on (100)ZnTe:P substrates. Journal of Crystal Growth, 2003, 248, 37-42.	1.5	10
158	Surface morphology of evaporated CuInS <sub>2</sub> thin films grown by single source thermal evaporation technique. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1486-1487.	2.1	10
159	The Structural and Optical Characterization of MBE-ZnSe Layer Grown on High-Quality VGF-ZnTe Substrate. Physica Status Solidi (B): Basic Research, 2002, 229, 127-131.	1.5	1
160	Deep Levels in Br-Doped ZnSe Single Crystals Grown by Physical Vapor Transport. Physica Status Solidi (B): Basic Research, 2002, 229, 291-295.	1.5	4
161	Optical Characterization of the ZnTe Pure-Green LED. Physica Status Solidi (B): Basic Research, 2002, 229, 977-980.	1.5	35
162	Optical Characterization of High Quality ZnTe Substrate. Physica Status Solidi A, 2002, 192, 218-223.	1.7	4

#	ARTICLE	IF	CITATIONS
163	Nonradiative and Radiative Recombination Processes of ZnS Epitaxial Layers. <i>Physica Status Solidi A</i> , 2002, 192, 230-235.	1.7	0
164	Growth of CuInS <sub>2</sub> crystals by a hot-press method. <i>Journal of Crystal Growth</i> , 2002, 236, 253-256.	1.5	27
165	Crystal growth of AgIn <sub>1-x</sub> Ga <sub>x</sub> Se <sub>2</sub> crystals grown by a vertical gradient freeze method. <i>Journal of Crystal Growth</i> , 2002, 236, 257-260.	1.5	18
166	Growth and characterization of codoping of ZnSe:Cl with Li grown by molecular beam epitaxy on GaAs. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 166-171.	2.7	5
167	Optical characterization of native defects in ZnSe substrate. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 299-306.	2.7	11
168	Optical and electrical properties of AgIn(SSe) <sub>2</sub> crystals. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 349-356.	2.7	25
169	Photoluminescence spectra of CuGaSe <sub>2</sub> crystals. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 357-363.	2.7	12
170	Optical properties of high-quality CuGaSe <sub>2</sub> epitaxial layers examined by piezoelectric photoacoustic spectroscopy. <i>Solar Energy Materials and Solar Cells</i> , 2001, 67, 173-178.	6.2	2
171	Photoacoustic Spectra for Porous Silicon Using Piezoelectric Transducer and Microphone. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 3610-3613.	1.5	3
172	Sharp band edge photoluminescence of high-purity CuInS <sub>2</sub> single crystals. <i>Applied Physics Letters</i> , 2001, 78, 742-744.	3.3	75
173	Growth of Bulk-ZnS by Solid Phase Recrystallization. <i>Physica Status Solidi A</i> , 2000, 180, 183-187.	1.7	7
174	Nonradiative Carrier Recombination Centers of Cl-Doped ZnSe Epitaxial Layers. <i>Physica Status Solidi A</i> , 2000, 180, 201-205.	1.7	5
175	Photoluminescence and photoacoustic spectra of N-doped ZnSe epitaxial layers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2000, 214-215, 572-575.	1.5	8
176	Crystal growth and photoluminescence of CuIn <sub>x</sub> Ga <sub>1-x</sub> Se <sub>2</sub> alloys. <i>Journal of Crystal Growth</i> , 2000, 211, 476-479.	1.5	26
177	Crystallization of Amorphous GeSe <sub>2</sub> Semiconductor by Isothermal Annealing without Light Radiation. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 1058-1061.	1.5	11
178	Temperature variation of nonradiative carrier recombination processes in high-quality CuGaSe <sub>2</sub> thin films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2000, 77, 259-261.	3.3	11
179	Piezoelectric Photoacoustic and Photoluminescence Properties of CuIn <sub>x</sub> Ga <sub>1-x</sub> Se <sub>2</sub> Alloys. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 3171-3174.	1.5	7
180	Optical characterizations of CuInSe <sub>2</sub> epitaxial layers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1999, 86, 4354-4359.	2.5	23

#	ARTICLE	IF	CITATIONS
181	Piezoelectric photoacoustic spectra of CuInSe <sub>2</sub> thin film grown by molecular beam epitaxy. Thin Solid Films, 1999, 343-344, 591-593.	1.8	3
182	Deep levels in ZnSe epitaxial layers examined by piezoelectric photoacoustic spectroscopy. Journal of Crystal Growth, 1998, 184-185, 1151-1154.	1.5	5
183	Shallow donor levels of Li-doped ZnSe single crystals. Microelectronic Engineering, 1998, 43-44, 683-688.	2.4	1
184	Photoacoustic spectra of zincselenide thin films grown by molecular beam epitaxy. Microelectronic Engineering, 1998, 43-44, 689-693.	2.4	0
185	Nonradiative Carrier Recombination in p-Type ZnSe Thin Films Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 1998, 210, 491-495.	1.5	6
186	Photoacoustic Study of The Effect of 0.9 eV Light Illumination in Semi-Insulating GaAs. Materials Research Society Symposia Proceedings, 1997, 484, 601.	0.1	0
187	Piezoelectric Photoacoustic Spectra In CuGaSe <sub>2</sub> Thin Films Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1997, 485, 151.	0.1	0
188	The Effects Of Substitutional Alkaline Metals In Zinc Vacancy Of Zincselenide Single Crystals Grown By The Sublimation Method. Materials Research Society Symposia Proceedings, 1996, 442, 593.	0.1	1
189	Temperature dependence of luminescence in ZnSe. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 68-71.	3.5	6
190	Photoluminescence of Zincselenide Single Crystals Grown by the Sublimation Method. Japanese Journal of Applied Physics, 1995, 34, 6331-6333.	1.5	6
191	Impurity Levels of Alkaline Metals in Zincselenide Single Crystals Examined by Photoluminescence. Japanese Journal of Applied Physics, 1995, 34, 61-65.	1.5	8
192	Electrical Properties of Fluorine Doped Tin Dioxide Film Grown by Spray Method. Materials Science Forum, 0, 725, 281-284.	0.3	2
193	Structural and Electronic Structure of SnO <sub>2</sub> by the First-Principle Study. Materials Science Forum, 0, 725, 265-268.	0.3	4
194	Gate-Length Dependent Radiation Damage in 2-MeV Electron-Irradiated Si <sub>1-x</sub> Ge <sub>x</sub> S/D p-MOSFETs. Materials Science Forum, 0, 725, 235-238.	0.3	0
195	Growth of CuInGaSe <sub>2</sub> Films by RF Sputtering Using CuInGaSe <sub>2</sub> Single Phase Target. Applied Mechanics and Materials, 0, 372, 571-574.	0.2	0
196	Photovoltaic Systems in University of Miyazaki. Applied Mechanics and Materials, 0, 372, 555-558.	0.2	0
197	Surface Morphology of Transparent Conductive ZnO Film Grown by DC Sputtering Method. Advanced Materials Research, 0, 894, 403-407.	0.3	4
198	Lead-free tin halide perovskite solar cells beyond 10 % efficiency. , 0, , .		0